CD4011B, CD4012B, CD4023B Types

COS/MOS NAND Gates

High-Voltage Types (20-Volt Rating)

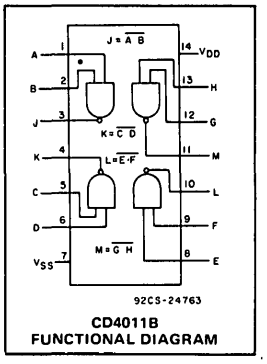
Quad 2 Input – CD4011B
Dual 4 Input – CD4012B
Triple 3 Input – CD4023B

RCA-CD4011B, CD4012B, and CD4023B NAND gates provide the system designer with direct implementation of the NAND function and supplement the existing family of COS/MOS gates. All inputs and outputs are buffered.

The CD4011B, CD4012B, and CD4023B types are supplied in 14-lead hermetic dual-in-line ceramic packages (D and F suffixes), 14-lead dual-in-line plastic packages (E suffix), 14-lead ceramic flat packages (K suffix), and in chip form (H suffix).

Features:

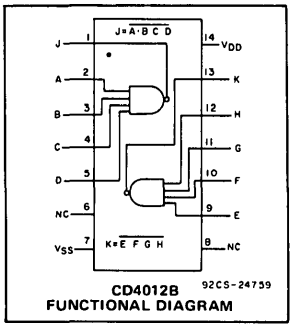
- **Propagation delay time = 60 ns (typ.) at C_L = 50 pF, V_{DD} = 10 V**
- **Buffered inputs and outputs**
- **Standardized symmetrical output characteristics**
- **Maximum input current of 1 μA at 18 V over full package temperature range; 100 nA at 18 V and 25°C**
- **100% tested for quiescent current at 20 V**
- **5-V, 10-V, and 15-V parametric ratings**
- **Noise margin (over full package temperature range:**
  1 V at V_{DD} = 5 V
  2 V at V_{DD} = 10 V
  2.5 V at V_{DD} = 15 V
- **Meets all requirements of JEDEC Tentative Standard No.13A, "Standard Specifications for Description of "B" Series CMOS Devices"**



CD4011B
FUNCTIONAL DIAGRAM

MAXIMUM RATINGS, *Absolute-Maximum Values*

DC SUPPLY-VOLTAGE RANGE, (V_{DD}) (Voltages referenced to V_{SS} Terminal)	−0.5 to +20 V
INPUT VOLTAGE RANGE, ALL INPUTS	−0.5 to V_{DD} +0.5 V
DC INPUT CURRENT, ANY ONE INPUT	±10 mA
POWER DISSIPATION PER PACKAGE (P_D)	
For T_A −40 to +60°C (PACKAGE TYPE E)	500 mW
For T_A +60 to +85°C (PACKAGE TYPE E)	Derate Linearly at 12 mW/°C to 200 mW
For T_A −55 to +100°C (PACKAGE TYPES D,F)	500 mW
For T_A +100 to +125°C (PACKAGE TYPES D, F)	Derate Linearly at 12 mW/°C to 200 mW
DEVICE DISSIPATION PER OUTPUT TRANSISTOR FOR T_A FULL PACKAGE TEMPERATURE RANGE (All Package Types)	100 mW
OPERATING TEMPERATURE RANGE (T_A)	
PACKAGE TYPES D, F, H	−55 to +125°C
PACKAGE TYPE E	−40 to +85°C
STORAGE TEMPERATURE RANGE (T_{stg})	−65 to +150°C
LEAD TEMPERATURE (DURING SOLDERING)	
At distance 1/16 ± 1/32 inch (1.59 ± 0.79 mm) from case for 10 s max	+265°C

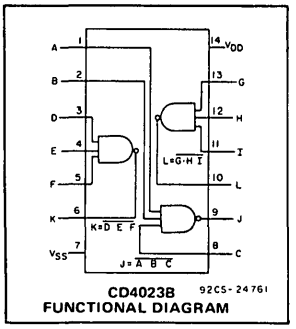


CD4012B
FUNCTIONAL DIAGRAM

RECOMMENDED OPERATING CONDITIONS

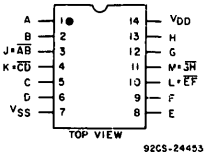
For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIMITS		UNITS
	MIN.	MAX.	
Supply-Voltage Range (For T_A = Full Package Temperature Range)	3	18	V

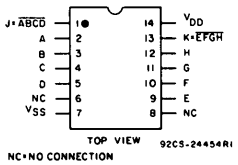


CD4023B
FUNCTIONAL DIAGRAM

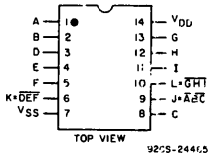
TERMINAL ASSIGNMENTS



CD4011B



CD4012B



CD4023B

STATIC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	CONDITIONS			LIMITS AT INDICATED TEMPERATURES (°C) Values at −55, +25, +125 Apply to D,F,H Packages Values at −40, +25, +85 Apply to E Package							UNITS
									+25		
	V_O (V)	V_{IN} (V)	V_{DD} (V)	−55	−40	+85	+125	Min.	Typ.	Max.	
Quiescent Device Current, I_{DD} Max.	–	0,5	5	0.25	0.25	7.5	7.5	–	0.01	0.25	μA
	–	0,10	10	0.5	0.5	15	15	–	0.01	0.5	
	–	0,15	15	1	1	30	30	–	0.01	1	
	–	0,20	20	5	5	150	150	–	0.02	5	
Output Low (Sink) Current I_{OL} Min	0.4	0,5	5	0 64	0.61	0.42	0.36	0 51	1	–	mA
	0.5	0,10	10	1.6	1.5	1 1	0.9	1 3	2.6	–	
	1.5	0,15	15	4 2	4	2.8	2.4	3.4	6.8	–	
Output High (Source) Current, I_{OH} Min.	4.6	0,5	5	−0.64	−0.61	−0.42	−0.36	−0.51	−1	–	
	2.5	0,5	5	−2	−1.8	−1 3	−1 15	−1 6	−3.2	–	
	9.5	0,10	10	−1.6	−1.5	−1.1	−0.9	−1.3	−2.6	–	
	13.5	0,15	15	−4 2	−4	−2 8	−2 4	−3 4	−6.8	–	
Output Voltage Low-Level, V_{OL} Max.	–	0,5	5	0 05				–	0	0.05	V
	–	0,10	10	0.05				–	0	0.05	
	–	0,15	15	0.05				–	0	0 05	
Output Voltage High-Level, V_{OH} Min.	–	0,5	5	4 95				4.95	5	–	
	–	0,10	10	9.95				9.95	10	–	
	–	0,15	15	14.95				14.95	15	–	
Input Low Voltage, V_{IL} Max.	4.5	–	5	1 5				—	—	1.5	V
	9	–	10	3				—	—	3	
	13.5	–	15	4				–	—	4	
Input High Voltage, V_{IH} Min.	0.5,4.5	–	5	3.5				3.5	—	—	
	1,9	–	10	7				7	—	—	
	1.5,13.5	–	15	11				11	—	—	
Input Current I_{IN} Max.		0,18	18	±0 1	±0.1	±1	±1	–	$±10^{-5}$	±0.1	μA

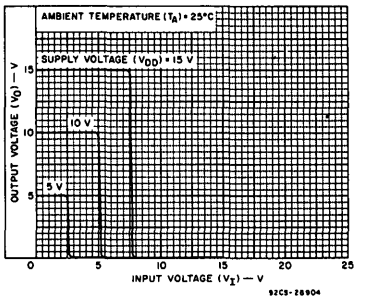


Fig.1 – Typical voltage transfer characteristics.

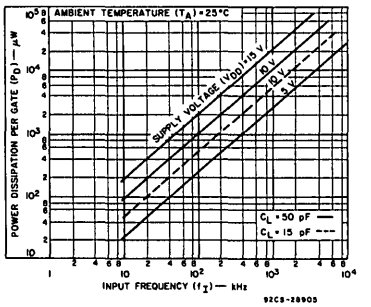


Fig.2 – Typical power dissipation characteristics.

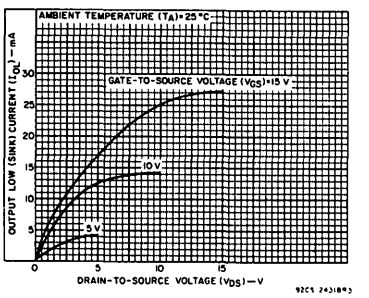


Fig.3 – Typical output low (sink) current characteristics.

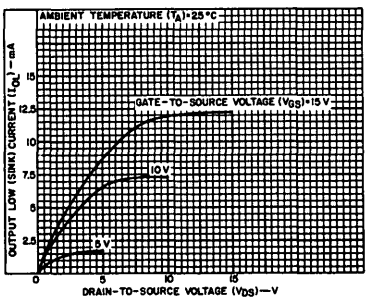


Fig.4 – Minimum output low (sink) current characteristics.

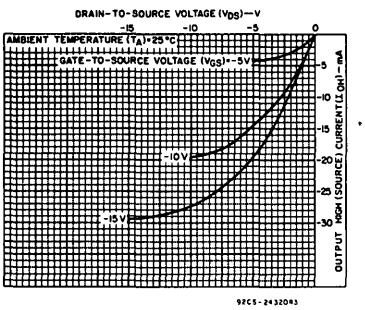


Fig.5 – Typical output high (source) current characteristics.

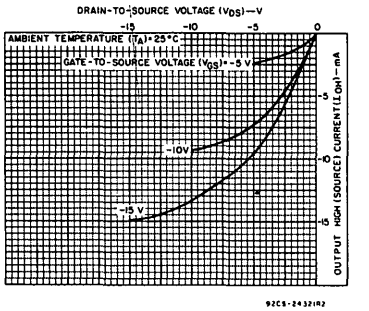


Fig.6 – Minimum output high (source) current characteristics.

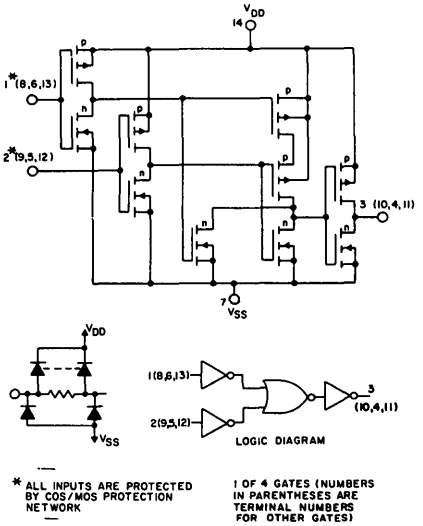


Fig.7 – Schematic and logic diagrams for CD4011B.

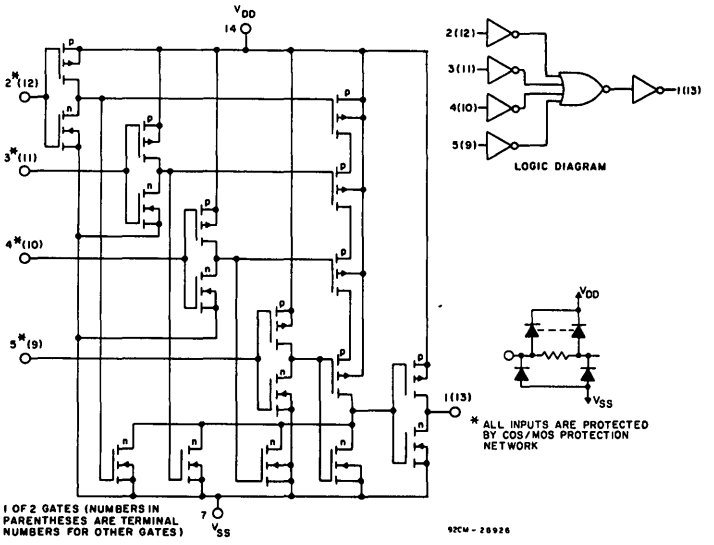


Fig.8 – Schematic and logic diagrams for CD4012B.

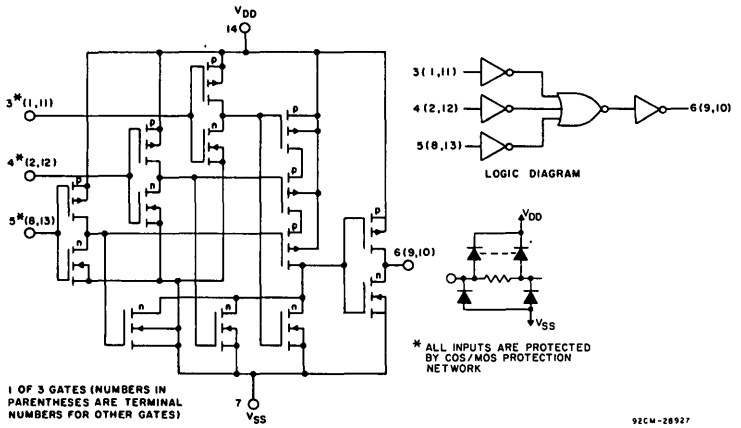


Fig. 9 – Schematic and logic diagrams for CD4023B.

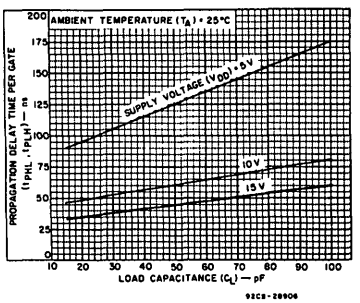


Fig.10 – Typical propagation delay time per gate as a function of load capacitance.

DYNAMIC ELECTRICAL CHARACTERISTICS

At T_A = 25°C; Input t_r, t_f = 20 ns, C_L = 50 pF, R_L = 200kΩ

CHARACTERISTIC	TEST CONDITIONS	ALL TYPES LIMITS		UNITS
	V_{DD} VOLTS	TYP.	MAX.	
Propagation Delay Time, t_{PHL}, t_{PLH}	5	125	250	ns
	10	60	120	
	15	45	90	
Transition Time, t_{THL}, t_{TLH}	5	100	200	ns
	10	50	100	
	15	40	80	
Input Capacitance, C_{IN}	Any Input	5	7.5	pF

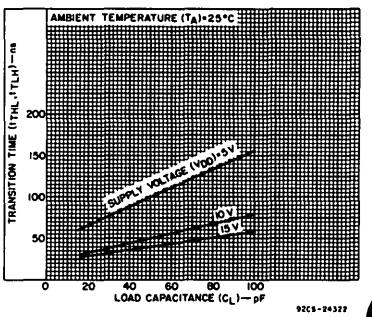


Fig.11 – Typical transition time as a function of load capacitance.

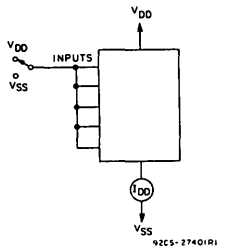


Fig. 12 – Quiescent-device-current test circuit.

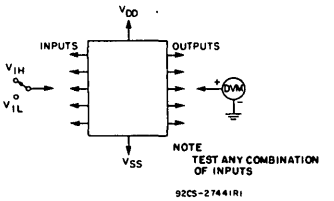


Fig. 13 – Input-voltage test circuit.

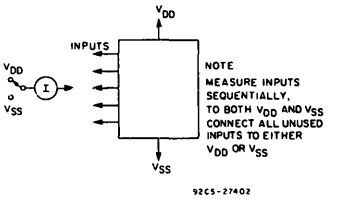
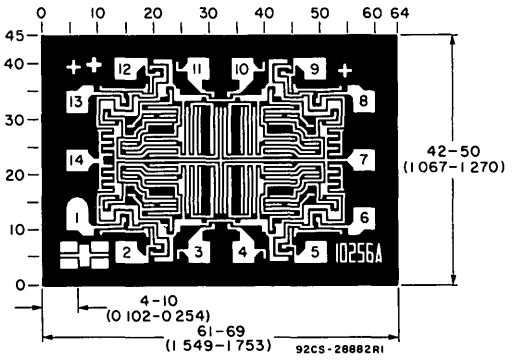
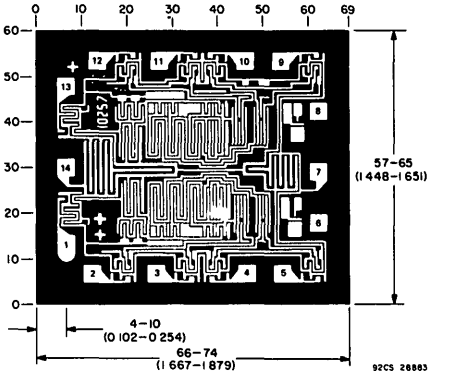


Fig. 14 – Input-current test circuit.

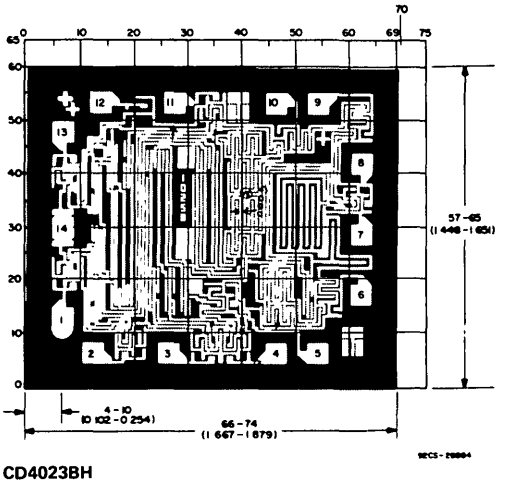
CHIP PHOTOGRAPHS
Dimensions and Pad Layouts



CD4011BH



CD4012BH



CD4023BH

Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils (10^{-3} inch).

The photographs and dimensions of each COS/MOS chip represent a chip when it is part of the wafer. When the wafer is cut into chips, the cleavage angles are 57° instead of 90° with respect to the face of the chip. Therefore, the isolated chip is actually 7 mils (0.17mm) larger in both dimensions